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Information Disclosure Statement by Applicant				Applicant: Cyril Guedj et al.			
(Use several sheets if necessary)				Filed: December 21, 2004		Group: <del>unknown</del> 2878	
<b>U.S. Patent Documents</b>							
Init.		Document No.	Date	Name	Class	Subclass	Filing Date
QL	A	5,682,037	10/28/97	de Cesare et al.			
QL	B	6,018,187	01/25/00	Theil et al.			
QL	C	6,114,739	09/05/00	Theil et al.			
<b>Foreign Documents</b>							
							Translation
Init.		Document No.	Date	Country	Class	Subclass	Yes No
QL	D	0 726 605	06.02.96	Europe	H01L 31	103	X
QL	E	1 050 907	02.05.00	Europe	H01L 27	146	X
<b>Other Documents (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
QL	F	Afanas'ev et al., "Photodetector structures based on amorphous hydrogenated silicon with nanocrystalline inclusions", December 2001, The Optical Society of America, J. Opt. Technol., Vol. 68, No. 12, pp 949-951.					
	G	Chatterjee et al., "The origin of current gain under illumination in amorphous silicon <i>n-i-p-i-n</i> structures", February 15, 2000, Journal of Applied Physics, Vol. 87, No. 4, pp. 1874-1881.					
	H	Meaudre et al., "Midgap density of states in hydrogenated polymorphous silicon", July 15, 1999, Journal of Applied Physics, Vol. 86, No. 2, pp. 946-950.					
	I	Morral, et al. "In situ investigation of polymorphous silicon deposition", 2000, Journal of Non-Crystalline Solids 266-269, pp. 48-53.					
	J	Morral et al., "Structure of plasma-deposited polymorphous silicon", 2002, Journal of Non-Crystalline Solids 299-302, pp. 284-289.					
	K	Poissant et al., "Metastability study and optimization of polymorphous silicon solar cells: the state-of-the-art", 2002, Journal of Non-Crystalline Solids 299-302, pp. 1173-1178.					
	L	Razeghi et al., "Semiconductor ultraviolet detectors", May 15, 1996, J. Appl. Phys., Vol. 79, No. 10, pp 7433.					
	M	Topic et al., "Adjustable ultraviolet-sensitive detectors based on amorphous silicon", April 16, 2001, Applied Physics Letters, Vol. 78, No. 16, pp. 2387-2389					
QL	N	Voz et al., "Thin-Film transistors with polymorphous silicon active layer", 2002, Journal of Non-Crystalline Solids 299-302, pp. 1345-1350.					
Examiner /Que Tan Le/					Date Considered 10/24/2006		
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.							